## Outlines

- <u>History of Conjugated Polymers</u>
- Electronic Structures of Conjugated Polymers
- **Polymer Light-emitting Diodes**
- **Polymer-based Thin Film Transistors**
- Polymer-based Photovoltaics
- **Polymers for Memory devices**

## Device Applications of Donor-Acceptor Conjugated Polymers in My Group



**Polymer Thin Film Transistors** 

**Polymer Memory Devices** 

#### Humanity's core problems in 2050





| 2003 | 6.3  | Billion People        |
|------|------|-----------------------|
| 2050 | 8-10 | <b>Billion People</b> |

Source: Richard Smalley, Energy & Nanotechnology Conference, Houston; Christoph Brabec; Konarka .

能源之種類

- 傳統能源:
  - 石化燃料(煤[230]、石油[45]、天然氣[60])
  - 火力
  - 核能[鈾:75] 註:[]為預估使用年限,單位--年
- 再生能源:
  - 太陽能(太陽光發電、太陽熱能)
  - 風力發電
  - 生質能(廢棄物發電、沼氣發電、生質物轉化、生質物汽化發電.....)
  - 地熱發電
  - 小水力發電
  - 海洋能(波浪發電、潮汐發電、海洋溫差)



Hydroelectric 1.2 TW technically feasible

0.6 TW installed capacity

- Tak

#### **Renewable energies**









Credit: Christoph Brabec, Konarka

Solar 1 x 10<sup>5</sup> TW at Earth surface 10,000 TW (technical value)



太陽光發電(光伏發電, Photovoltaic, PV)之特點

1. 太陽電池通常為一種固態半導體元件,將光能直接

轉換為(直流)電能,但本身不儲存能量。

2. 太陽電池使用方便、無廢棄物、無污染、無轉動部

份、無噪音、可阻隔輻射熱、或可設計為半透光。

- 3. 太陽電池模板壽命長久, 可達二十年以上。
- 4. 太陽電池外型尺寸可隨意變化,應用廣泛(小至消費

性產品--如計算機,大至發電廠皆實用)。

5. 太陽電池未來與建築物結合,將可普及化。

太陽能是免費、取之不盡、用之不竭之潔淨能源,但必須找到使用之方法。

## Future Trend-- Renewable Energy

# 太陽光熱發電將是未來電源供應主力



、陽每天照射到地表的能量,超過全人類30年能源需求!

# 太陽能發電之重要發展歷史

- ✤ 1954年 Bell Labs發展出砂太陽電池
  - (Chapin等人,轉換效率約6%)
- ≥ 1958年開始太空應用(GaAs)



- ▶ 1970年開始太陽光發電系統地面應用(Si)(能源危機)
   ▶ 1976年Carlson製作出第一個非晶薄膜太陽電池
   ▶ 1980年消費性薄膜太陽電池應用(a-Si, CdS/CdTe)
   ▶ 1990年與公用電力併聯之太陽光發電系統技術成熟 (Grid-Connected PV System, Si)(電力電子技術)
   ▶ 1992年起歐美、日各國推動PV補助獎勵
- ≫ 2000年建材一體型太陽電池應用(BIPV)



## History of Organic Solar Cells

| $\wedge$ | Some important milestones in the development of organic solar cells                 |
|----------|---|
| 1        |   |
| 2001     | -Ramos used <i>double-cable</i> polymers in PV cells.                               |
| 2001     | -Schmidt-Mende made a self-organised liquid crystalline solar cell of               |
|          | hexabenzocoronene and perylene.   |
| 2000     | -Peters / van Hal used oligomer-C <sub>60</sub> dyads/triads as the active material |
|          | in PV cells.  |
| 1995     | -Yu / Hall made the first bulk polymer/polymer heterojunction PV.                   |
| 1994     | -Yu made the first bulk polymer/C <sub>60</sub> heterojunction PV.                  |
| 1993     | - Sariciftci made the first polymer/C <sub>60</sub> heterojunction device.          |
| 1991     | -Hiramoto made the first dye/dye bulk heterojunction PV by co-sublimation.          |
| 1986     | -Tang published the first heterojunction PV device.                                 |
| 1964     | -Delacote observed a rectifying effect when magnesium phthalocyanines               |
|          | (CuPh) was placed between two different metalelectrodes.                            |
| 1958     | -Kearns and Calvin worked with magnesium phthalocyanines (MgPh),                    |
|          | measuring a photovoltage of 200 mV.   |
| 1906     | -Pochettino studied the photoconductivity of anthracene.                            |
| 1839     | -Becquerel observed the photoelectrochemical process.                               |
|          |   |

# <u>太陽能發電(Photovoltaic)原理</u>



| •太陽電池是以P 型與N       |
|--------------------|
| 型半導體材料接合構成的        |
| 裝置。                |
| • 當陽光照射太陽電池        |
| 時,半導體材料吸收光子        |
| 會產生電子-電洞對。         |
| • 分離正電荷(Hole)、負電   |
| 荷(Electron)會分別往正(P |
| 型)、負(N型)極方向移動      |
| 並且聚集。              |
| • 正、負極接上負載時,       |
| 將有電流流出,可以對負        |
| 載作功(燈泡會亮、馬達會       |
| 轉)。                |

太陽能電池種類



## Highest Solar Cell Efficiency Tables until 2006. 04

Table I. Confirmed terrestrial cell and submodule efficiencies measured under the global AM1.5 spectrum (1000  $\text{Wm}^{-2}$ ) at 25°C

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| Classification <sup>a</sup>              | Effic. <sup>b</sup><br>(%) | Area <sup>c</sup><br>(cm2) | V <sub>oc</sub><br>(V)    | J <sub>sc</sub><br>(mA/cm <sup>2</sup> ) | FF <sup>d</sup><br>(%) | Test Centre <sup>e</sup><br>(and Date) | Description   |
|--|----------------------------|----------------------------|---------------------------|--|------------------------|--|---|
| Silicon                                  |                            |                            |                           |  |                        |  |   |
| Si (crystalline)                         | $24.7\pm0.5$               | 4.00 (da)                  | 0.706                     | 42.2                                     | 82.8                   | Sandia (3/99)                          | UNSW PERL <sup>14</sup>                               |
| Si (multicrystalline)                    | $20.3\pm0.5$               | 1.002 (ap)                 | 0.664                     | 37.7                                     | 80.9                   | NREL (5/04)                            | FhG-ISE <sup>15</sup>                                 |
| Si (thin film transfer)                  | $16.6\pm0.4$               | 4.017 (ap)                 | 0.645                     | 32.8                                     | 78.2                   | FhG-ISE (7/01)                         | U. Stuttgart (45 µm thick) <sup>16</sup>              |
| Si (thin film submodule)                 | $9.4\pm0.3$                | 94.9 (ap)                  | <b>0.493</b> <sup>f</sup> | <b>26.0</b> <sup>f</sup>                 | 73.1                   | Sandia (4/06)                          | CSG Solar (1-2 μm on glass;<br>20 cells) <sup>5</sup> |
| III–V Cells                              |                            |                            |                           |  |                        |  |   |
| GaAs (crystalline)                       | $25.1\pm0.8$               | 3.91 (t)                   | 1.022                     | 28.2                                     | 87.1                   | NREL (3/90)                            | Kopin, AlGaAs window <sup>17</sup>                    |
| GaAs (thin film)                         | $24.5\pm0.5$               | 1.002 (t)                  | 1.029                     | 28.8                                     | 82.5                   | FhG-ISE (5/05)                         | Radboud U., NL <sup>18</sup>                          |
| GaAs (multicrystalline)                  | $18.2\pm0.5$               | 4.011 (t)                  | 0.994                     | 23.0                                     | 79.7                   | NREL (11/95)                           | RTI, Ge substrate <sup>19</sup>                       |
| InP (crystalline)                        | $21.9\pm0.7$               | 4.02 (t)                   | 0.878                     | 29.3                                     | 85.4                   | NREL (4/90)                            | Spire, epitaxial <sup>20</sup>                        |
| Thin Film Chalcogenide                   |                            |                            |                           |  |                        |  |   |
| CIGS (cell)                              | $18.4\pm0.5^{\rm g}$       | 1.04 (ap)                  | 0.669                     | 35.7                                     | 77.0                   | NREL (2/01)                            | NREL, CIGS on glass <sup>21</sup>                     |
| CIGS (submodule)                         | $16.6\pm0.4$               | 16.0 (ap)                  | $0.661^{f}$               | 33.4 <sup>f</sup>                        | 75.1                   | FhG-ISE (3/00)                         | U. Uppsala, 4 serial cells <sup>22</sup>              |
| CdTe (cell)                              | $16.5\pm0.5^{\rm g}$       | 1.032 (ap)                 | 0.845                     | 25.9                                     | 75.5                   | NREL (9/01)                            | NREL, mesa on glass <sup>23</sup>                     |
| Amorphous/Nanocrystalline Si             |                            |                            |                           |  |                        |  |   |
| Si (amorphous) <sup>h</sup>              | $9.5\pm0.3$                | 1.070 (ap)                 | 0.859                     | 17.5                                     | 63.0                   | NREL (4/03)                            | U. Neuchatel <sup>24</sup>                            |
| Si (nanocrystalline)                     | $10.1\pm0.2$               | 1.199 (ap)                 | 0.539                     | 24.4                                     | 76.6                   | JQA (12/97)                            | Kaneka $(2 \mu m \text{ on glass})^{25}$              |
| Photochemical                            |                            |                            |                           |  |                        |  | at 22° - 1965 - 6                                     |
| Dye sensitised                           | $10.4\pm0.3$               | 1.004 (ap)                 | 0.729                     | 21.8                                     | 65.2                   | AIST (8/05)                            | Sharp <sup>26</sup>                                   |
| Dye sensitised (submodule)               | $6.3\pm0.2$                | 26.5 (ap)                  | 6.145                     | 1.70                                     | 60.4                   | AIST (8/05)                            | Sharp <sup>6</sup>                                    |
| Organic                                  |                            |                            |                           |  |                        |  |   |
| Organic polymer <sup>i</sup>             | $3.0 \pm 0.1$              | 1.001 (ap)                 | 0.538                     | 9.68                                     | 52.4                   | AIST (3/06)                            | Sharp, fullerene derivative <sup>7</sup>              |
| Multijunction Devices                    |                            |                            |                           |  |                        |  |   |
| GaInP/GaAs/Ge                            | $32.0 \pm 1.5$             | 3.989 (t)                  | 2.622                     | 14.37                                    | 85.0                   | NREL (1/03)                            | Spectrolab (monolithic)                               |
| GaInP/GaAs                               | 30.3                       | 4.0 (t)                    | 2.488                     | 14.22                                    | 85.6                   | JQA (4/96)                             | Japan Energy (monolithic) <sup>27</sup>               |
| GaAs/CIS (thin film)                     | $25.8 \pm 1.3$             | 4.00 (t)                   | _                         | —  |                        | NREL (11/89)                           | Kopin/Boeing (4 terminal) <sup>28</sup>               |
| a-Si/µc-Si (thin submodule) <sup>i</sup> | $11.7\pm0.4$               | 14.23 (ap)                 | 5.462                     | 2.99                                     | 71.3                   | AIST (9/04)                            | Kaneka (thin film) <sup>29</sup>                      |

Prog. Photovolt: Res. Appl. 2006; 14:455–461 1

## Efficiency of Photovoltaic Devices

#### Measured Solar Cell Efficiency from 1975 to the present



From NREL, USA

### Requirement Trends of the Photovoltaic Industry



**Annual PV cell/module production** 

Estimation of present and future installed solar capacities

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太陽光發電之應用領域



## Solid State Organic Solar Cells

|               | Optical power $\Rightarrow$ electrical power   |
|---------------|--|
| Photovoltaics | FIGURES OF MERRIT:<br>Power conversion efficiency<br>Full solar intensities<br>Reliability |

High absorption in the visible spectrum

Have relaxed deposition requirements

can be manufactured in a low cost process

can be grown on thin and flexible substrate

can add value to existing product

**Challenge!** 

Current power conversion efficiencies are too low for commercial implementation

有機太陽光電技術

### Organic solar cells : three types





#### Organic double layer p/n cell



C. W. Tang, Appl. Phys. Lett. 1985, 48, 183.

#### **Bulk heterojunction solar cells**

Charge separation in nanostructured composite organic semiconductors





nanoscopic mixing of donor and acceptor to overcome ~10 nm exciton diffusion length

R. H. Friend et al., Nature 1995, **376**, 498 A. J. Heeger et al., Science 1995, **270**, 1789



## Structures and Principles of LED & Photovoltaic mode

#### LED mode

**Photovoltaic mode** 

A PV mode is the reverse of a LED. In PVs electrons are collected at the metal electrode and holes are collected at the ITO electrode.

# What & Why Is Organic Solid Phase Photovolta

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## **Polymer Based Solar Cell-Active layer**



# **Light Converting Processes**



### General Mechanism in Organic Photovoltaic Cells



- (1) Photon absoption (  $\eta$   $_{\rm A})$
- (2) Generation of excitons
- (3) Exciton diffusion (  $\eta_{\rm diff}$  )

(4) Hole-electron separation (  $\eta_{TC}$ )

(5) Carrier transport towards the electrode (  $\eta_{\rm tr}$  )

(6) Charge collection at the respective electrode(  $\eta$   $_{\rm CC}$ )

## General Scheme for Organic Photovoltaic Effect



### **Examples on Polymer Phtovoltaic Devices**



#### First Polymer-Polymer heterojunction PV

NATURE · VOL 376 · 10 AUGUST 1995



Energy conversion efficiency: 2.9 % Science 1995

### Plastic Solar Cells



A large area plastic solar cell running a small motor



MDMO-PPV:PCBM solar cell realized on a PET substrate

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# Applications



Converse to 2006 ITDI - 要社保证依障

### Polymer solution processed cells come in three 'flavors'



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Polymer solar cells





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建構高分子太陽能電池元件製程平台



# 標準元件製作流程

### **Procedure:**



太陽電池之 I-V曲線



ill Factor (F.F.) = (V<sub>mp</sub> x I<sub>mp</sub> / V<sub>oc</sub> x I<sub>sc</sub>) x 100% **、陽電池效率(Efficiency**; η) = (I<sub>sc</sub> x V<sub>oc</sub> x FF / 輸入日照功率) x 100%
輸入日照功率(W)=太陽電池面積(m<sup>2</sup>) ×日照強度(W/m<sup>2</sup>)
日照強度為1000 W/m<sup>2</sup>之最大輸出功率即為Wp
太陽電池開路、短路時皆不會燒燬



Air Mass (AM)- A measure of how much atmosphere sunlight must travel through to reach surface. The intensity is fixed at 100W/cm<sup>2</sup>.

**Open circuit voltage (V<sub>oc</sub>)** Voltage across the cell in sunlight when no current is flowing.

Short circuit voltage (I<sub>sc</sub>) Current flows through an solar cell when there is no external resistance.

**Maximum power point (mpp)** The maximum power is produced.

Fill Factor (FF)  $FF = \frac{I_{mpp}V_{mpp}}{I_{sc}V_{oc}}$  Power conversion  $\eta_e = \frac{I_{mpp}V_{mpp}}{P_{in}} = \frac{I_{sc}V_{oc}FF}{P_{in}}$ 

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## **Polymer Photovoltaic Structure**



## **Postproduction** induced P3HT:PCBM solar cells

#### **P3HT:PCBM solar cells**

|             | AM1.5 performance |      |     |     |  |  |  |  |  |
|-------------|-------------------|------|-----|-----|--|--|--|--|--|
| $J_{ m sc}$ | $V_{ m oc}$       | FF   | EQE | η   |  |  |  |  |  |
| 8.7         | 0.58              | 0.55 | 70  | 2.8 |  |  |  |  |  |
| 8.5*        | 0.55              | 0.60 | 70  | 3.5 |  |  |  |  |  |
| 9.4         | 0.61              | 0.53 | 58  | 3.0 |  |  |  |  |  |
| 7.2         | 0.62              | 0.62 | 58  | 2.7 |  |  |  |  |  |
| 11.1*       | 0.65              | 0.54 | =   | 4.9 |  |  |  |  |  |
| 9.5*        | 0.63              | 0.68 | -   | 5.0 |  |  |  |  |  |
| 10.6        | 0.61              | 0.67 | 63  | 4.4 |  |  |  |  |  |
| > 10**      | ~0.60             | -    | 73  | 4.4 |  |  |  |  |  |

\* measured at 80 mW/cm<sup>2</sup>; \*\* at 85 mW/cm<sup>2</sup>

- P. Schilinsky et al., Appl. Phys. Lett. 2002, 81, 3885.
- F. Padinger et al., Adv. Funct. Mater 2003, 13, 85.
- Y. Kim et al., Appl. Phys. Lett. 2005, 86, 063502.
- X. Yang et al., Nano Lett. 2005, **5**, 579.
- M. Reyes-Reyes et al., Appl. Phys. Lett. 2005 87, 083506
- W. Ma et al., Adv. Funct. Mater., 2005, **15**, 1617.
- G. Li et al., Nature Mater. 2005, 4, 864.
- Y. Kim et al., Nature Mater. 2006, 5, 197.







Yang Yang et al. Nature Mater. 2005, 4, 864.

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# **R&D** Focuses to Tackle Critical Issues

- New polymer design to enhance mobility & light harvesting
- Ordered BHJ structure with well-defined paths and limited width
- New device design to enhance Jsc or Voc
- Life time issues





## Current Challenges

The lower photocurrent is due to poor light absorption, generation and transport. The fill factor is due to poor transport and recombination.

#### • Improving light harvesting

Small band gap polymer, dye-sensitized materials, light-trapping structures

• Improving charge transport

Carrier mobility (10<sup>-2</sup>~10<sup>-5</sup> cm<sup>2</sup>/VS) is low

#### Control morphology

Processing condition, self organization, synthesis of D-A block copolymer, use of porous films as template

• Addressing manufacturing issue and improving stability

By encapsulating cells and more stable materials

• Understanding device function and limits to performance

## 國際發展比較-有機固態太陽光電

| 高分子-碳材太陽光電池技術  |  |                     |  |  |  |  |  |
|--|--|---------------------|--|--|--|--|--|
| Authors/Institutes   | Compositions                               | Efficiency (%)      |  |  |  |  |  |
| David L. Carroll/Wake Forest<br>University, USA/Kyungkon Kim/<br>KIST, Korea | ITO/PEDOT:PSS/P3HT:PCBM/LiF/AI             | 6.1                 |  |  |  |  |  |
| C. J. Brabec /Siemens (Konarka)<br>AU/A. Heeger/Konarka USA                  | ITO/PEDOT:PSS/P3HT:PCBM/AI                 | 5.68                |  |  |  |  |  |
| Kwanghee Lee /Pusan U., Korea/<br>A. Heeger                                  | ITO/PEDOT:PSS/P3HT:PCBM/TiO2/Al            | 5.8                 |  |  |  |  |  |
| A. Heeger/UC Santa Barbara ,<br>USA  | ITO/PEDOT:PSS/P3HT:PCBM/AI                 | 4.8-5.1/100 samples |  |  |  |  |  |
| N. S. Sariciftci /Linz<br>Austria  | ITO/PEDOT:PSS/MDMO-<br>PPV:PCBM/LiF/Al     | 3.5                 |  |  |  |  |  |
| Y. Yang /UCLA ,USA   | ITO/PEDOT:PSS/P3HT:PCBM/AI                 | 4.4/3.8             |  |  |  |  |  |
| R. A. J. Janssen/ECN<br>Netherlands  | ITO/PEDOT:PSS/MDMO-<br>PPV:[70]PCBM/LiF/Al | 3.0                 |  |  |  |  |  |
| ITRI   | ITO/PEDOT:PSS/P3HT:PCBM/Ca:Al              | 5.4                 |  |  |  |  |  |





## Prospects for high-efficiency (>10%) Polymer PV cells

- 1. New device designs: Ordered Bulk Heterojuctions
- Approach: Polymer Semiconductor/acceptor Order Heterojuction Structure
- 2. The high light-absorbing capabilities:
- Conjugated polymer and electron acceptor with lower band gap: 350-900 nm (3.5~1.4eV)
- Approach: Low Eg Polymer



- 3. Higher carrier mobilities:
- Approach:高分子mobilities > 0.01 cm<sup>2</sup>/Vs and Morphology control
  Chem. Mater. 2004, 16, 4533

## Four device architectures of conjugated polymer–based PV cells



- Single Layer(a): Low EQE(0.1~1%) due to exciton recombination; low carrier mobility
- Bilayers (b) : PA-PPV/TiO<sub>2</sub> 25% EQE, 3.9 % power efficiency (435 nm);

PPV/BBL 66%% EQE, 2% power efficiency

• Bulk heterojunction (c) (d):

PPV/C60 Derivatives 70% EQE, 3.5% power efficiency

Chem. Mater. 2004, 16, 4533

## Organic Photovoltaic Device Architectures



# Organic Photovoltaic Device Architectures

#### **Bulk Heterojunction Devices**



## Organic Semiconductors Used in Solar Cells









a-sexithiophene

# Some of the Approaches in MCL

# 1. Better packing conducting polymer

— Stereo-regular conducting polymer (no micro-structure defects)



- Tightly-packing conducting polymer but still maintain its processbility
- High mobility conducting polymer design with good solubility



### Absorption Spectrum of Organic Materials



Photon reflux from the sun (AM 1.5)

## P3HT:PCBM Solar Cells

#### Different annealing time



 $V_{oc} = 0.61 V$  FF = 0.67

I<sub>sc</sub> = 10.6 mA/cm<sup>2</sup> PCE = 4.37 %

### PPV:PCBM Solar Cells



 $V_{oc} = 0.82 V$  FF = 0.61

I<sub>sc</sub> = 5.25 mA/cm<sup>2</sup> PCE = 2.5 %

APL 2001, 78, 841

#### Design strategy for low band gap: Donor-Acceptor polymers

increase the double bond character of the single bonds:



## D-A Conjugated Alternating Polymers: PCBM Solar Cells





- $V_{oc} = 0.72 V$  FF = 0.37
- I<sub>sc</sub> = 3.1 mA/cm<sup>2</sup> PCE = 1 %

 $V_{oc} = 0.76 V$  FF = 0.49  $I_{sc} = 4.31 \text{ mA/cm}^2$  PCE = 1.6 %



 $V_{oc} = 0.72 V$  FF = 0.46  $I_{sc} = 4.66 \text{ mA/cm}^2$  PCE = 2.2 %



 $V_{oc} = 0.56 V$  FF = 0.49  $I_{sc} = 3.6 \text{ mA/cm}^2$  PCE = 0.51 %

### D-A Conjugated Alternating Polymers: PCBM or C70 Solar Cells



## D-A Conjugated Alternating Polymers: PCBM Solar Cells



 $V_{\rm oc}$  = 0.72 V

 $I_{sc} = 3.1 \text{ mA/cm}^2$ 

**FF = 0.37** 

**PCE** = 1 %



 $V_{\rm oc} = 0.77 \ V$ 

 $I_{sc} = 3.4 \text{ mA/cm}^2$ 

FF = 0.42

**PCE = 0.2 %** 



 $V_{oc} = 0.59 V$  FF = 0.39  $I_{sc} = 2.6 \text{ mA/cm}^2$  PCE = 0.6 %



 $V_{\rm oc}$  = 0.56 V

 $I_{sc} = 3.5 \text{ mA/cm}^2$ 

FF = 0.58

**PCE** = 1.1 %



 $V_{oc} = 0.61 V$  FF = 0.24  $I_{sc} = 0.2 \text{ mA/cm}^2$  PCE = 0.02 %



#### Table 1. Molecular Weights, FET Mobility, and Optical and Electrochemical Properties of Various Polymers

|      | $M_{\rm w}~({ m PDI})$ | $\lambda_{max}$ (film) | $\alpha^a$ (cm <sup>-1</sup> ) | $E_8^{opt}$ (eV | () $E_{\text{ox}} (\mathbf{V})^b$ | IP (eV) (HOMO) | EA (eV) (LUMO) | ) $\mu_{\mathbf{h}}^{c}$ (cm | 1²/(V s))                 | on/off <sup>c</sup>                         |
|------|------------------------|------------------------|--------------------------------|-----------------|-----------------------------------|----------------|----------------|------------------------------|---------------------------|---|
| P1   | 25200 (1.52)           | 490                    | $6.3 \times 10^5$              | 2.10            | 0.71                              | 5.17           | 3.07           | $3.7 \times 10^{-4}$         |                           | $5.2 \times 10^3$                           |
| P2   | 21800 (1.97)           | 510                    | $3.0 \times 10^{5}$            | 2.10            | 0.72                              | 5.18           | 3.08           | $1.5 \times 10^{-4}$         |                           | $1.4 \times 10^{4}$                         |
| P3   | 48700 (2.19)           | 510                    | $9.9 \times 10^{5}$            | 2.08            | 0.64                              | 5.1            | 3.02           | $8.3 \times 10^{-4}$         |                           | $9.1 \times 10^{4}$                         |
| P4   | 29300 (1.87)           | 508                    | $9.4 \times 10^{5}$            | 2.11            | 0.72                              | 5.18           | 3.07           | $3.0 \times 10^{-3}$ (       | $9.9 \times 10^{-4})^{d}$ | $1.3 \times 10^{6} (6.5 \times 10^{5})^{d}$ |
| P3HT | 47000 (2.45)           | 552                    | $1.2 \times 10^{6}$            | 1.90            | 0.74                              | 5.20           | 3.30           | $6.5 \times 10^{-2}$         |                           | $1.3 \times 10^{3}$                         |

<sup>*a*</sup> Absorption coefficient was determined at  $\lambda_{max}$  in THF. <sup>*b*</sup>  $E_{ox}$  is the onset potential of oxidation of polymer. <sup>*c*</sup> Thin-film FETs were fabricated from 1 wt % *o*-DCB solutions. <sup>*d*</sup> CHCl<sub>3</sub> solutions used instead of *o*-DCB.

High absorption coefficient in comparison to P3HT

*Ko et al., Macromolecules* **2008**, 41, 5519



| rable i | 7. Molecular #       | reighte, ett i met         | mity, optical and ne                      |                        | Tues of Valie       | do i olymeio |           |   |
|---------|----------------------|----------------------------|---|------------------------|---------------------|--------------|-----------|---|
|         | M <sub>w</sub> (PDI) | $\lambda_{\rm max}$ (film) | $\alpha$ ( $\times$ 10 $^{5}$ cm $^{-1})$ | Eg <sup>opt</sup> (eV) | E <sub>∞</sub> °(V) | HOMO (eV)    | LUMO (eV) | ļ |

|    | M <sub>w</sub> (PDI) | $\lambda_{\max}$ (film) | $\alpha$ ( $	imes$ 10 <sup>5</sup> cm <sup>-1</sup> ) | Eg <sup>opt</sup> (eV) | E <sub>∞</sub> °(V) | HOMO (eV) | LUMO (eV) | $\mu_{\rm h}~({\rm cm^2/Vs})$ | on/off              |
|----|----------------------|-------------------------|---|------------------------|---------------------|-----------|-----------|-------------------------------|---------------------|
| P1 | 26300 (1.55)         | 520                     | $\frac{11^a(1.6)^b}{7.7^{\;a}(1.4)^b}$                | 1.76                   | 1.00                | -5.46     | -3.56     | $7.0 \times 10^{-4}$          | $1.3 \times 10^{5}$ |
| P2 | 38600 (1.74)         | 590                     |   | 1.70                   | 0.97                | -5.43     | -3.66     | $3.4 \times 10^{-3}$          | $5.6 \times 10^{6}$ |

Ko et al, J. Am. Chem. Soc. 2008, in press

## Design Rules for Donors in Solar Cell - Towards 10 % PCE



To get PCE >10%

Bandgap of donor polymer < 1.74 eV & LUMO < -3.92 eV



poor PV efficiency

### The importance of HOMO/LUMO level on the Photovoltaic Devices



Scharber et al., Adv. Mater. 2006, 18, 789

## Importance of Polymer Morphology on Photovoltaic Efficiency



Figure 2. The AFM height (a-d) and simultaneously taken phase (e-h) images of the MDMO-PPV/PCBM composite films of 90 (a,e), 30 (b,f), 67 (c,g), and 50 wt-% PCBM (d,b). Height bar (maximum peak-to-valley) represents 20 nm (a), 10 nm (b), 3 nm (c), and 3 nm (d). The size of the images is 2.0  $\mu$ m ×2.0  $\mu$ m.



Morphology determining parameters: The spin casting solvent The composition between polymer and fullerene The solution concentration The controlled phase separation and crystallization induced by thermal annealing The chemical structure of the materials

Adv. Funct. Mater. 2004, 14, No. 5, May J. Mater. Chem., 2006, 16, 45-61 H. Spanggaard, F.C. Krebs / Solar Energy Materials & Solar Cells 83 (2004) 125-146

## 2. Defined transport path

From Polymer:



10.0kV X40.000 100nm WD 12.5m

From Nanocrystals

## **Control of Surface Grown ZnO**

